



## General Description

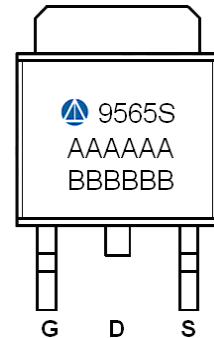
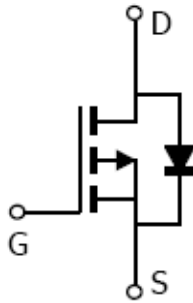
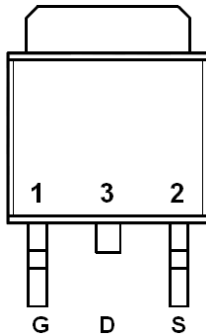
AFP9565S, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

## Features

- -40V/ -8.6A,  $R_{DS(ON)} = 58m\Omega @ V_{GS} = -10V$
- -40V/ -6.2A,  $R_{DS(ON)} = 86m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- TO-252-2L package design

## Pin Description ( TO-252-2L )



## Application

- Backlight Inverter for LCD Display
- Full Bridge DC/DC Converter
- LED Display
- Load Switch
- CCFL Inverter

## Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP9565ST252RG	9565S	TO-252-2L	Tape & Reel	2500 EA

※ A Lot code

※ B Date code

※ AFP9565ST252RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-40	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-17
		T <sub>A</sub> =70°C	-11
Pulsed Drain Current	I <sub>DM</sub>	-30	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	-8	A
Single Pulse Avalanche Current	I <sub>AS</sub>	-30	A
Avalanche Energy	E <sub>AS</sub>	35	mJ
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	40
		T <sub>A</sub> =70°C	15
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	62.5	°C/W

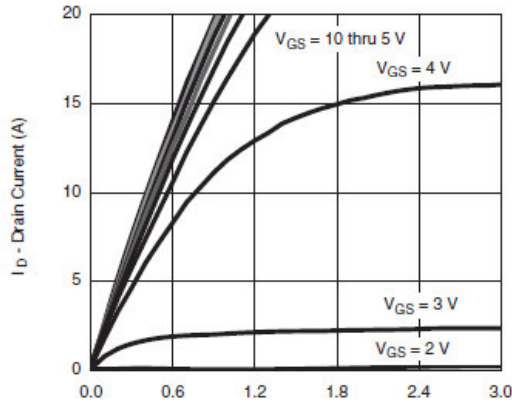
**Electrical Characteristics**

(T<sub>A</sub>=25°C Unless otherwise noted)

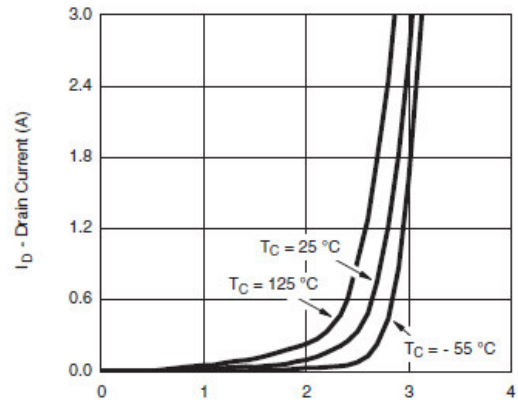
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = -250uA	-40			V
Gate Threshold Voltage	V <sub>G(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1.0		-2.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -32V, V <sub>GS</sub> =0V			-1	uA
		V <sub>DS</sub> = -32V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-20	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -5V, V <sub>GS</sub> = -10V	-17			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -8.6A		48	58	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6.2A		70	86	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -5A		20		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -2A, V <sub>GS</sub> =0V		-0.8	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V I <sub>D</sub> = -5.0A		10	16	nC
Gate-Source Charge	Q <sub>gs</sub>			3		
Gate-Drain Charge	Q <sub>gd</sub>			5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V f=1MHz		850		pF
Output Capacitance	C <sub>oss</sub>			100		
Reverse Transfer Capacitance	C <sub>rss</sub>			80		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-20V, R <sub>L</sub> =5Ω I <sub>D</sub> =-4.0A, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =1Ω		45	65	ns
	t <sub>r</sub>			100	150	
Turn-Off Time	t <sub>d(off)</sub>			25	40	
	t <sub>f</sub>			12	20	



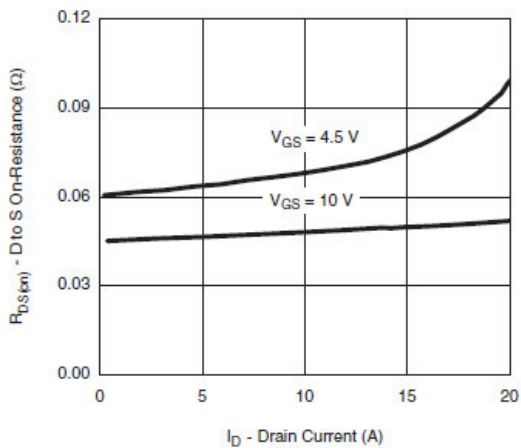
## Typical Characteristics



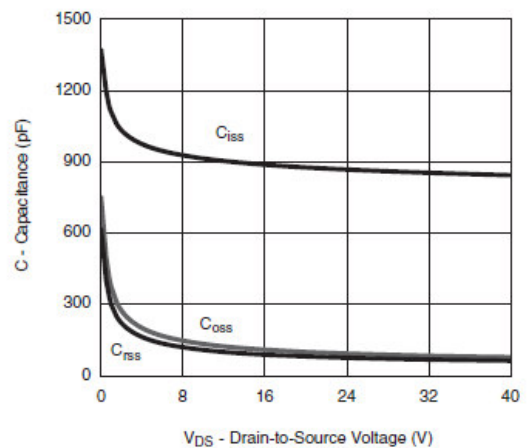
$V_{DS}$  - Drain-to-Source Voltage (V)  
**Output Characteristics**



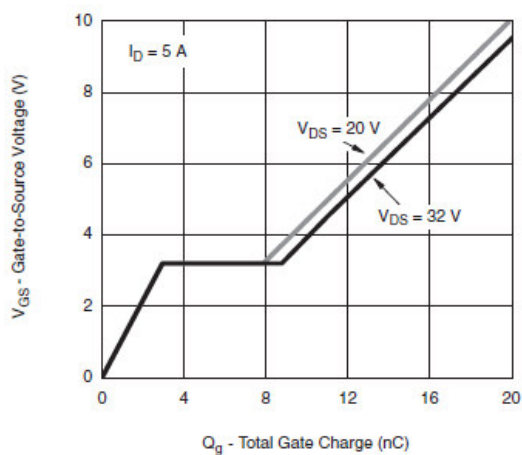
$V_{GS}$  - Gate-to-Source Voltage (V)  
**Transfer Characteristics**



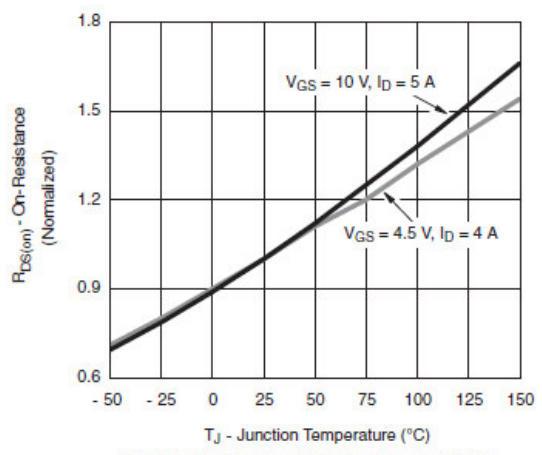
$I_D$  - Drain Current (A)  
**On-Resistance vs. Drain Current and Gate Voltage**



$V_{DS}$  - Drain-to-Source Voltage (V)  
**Capacitance**



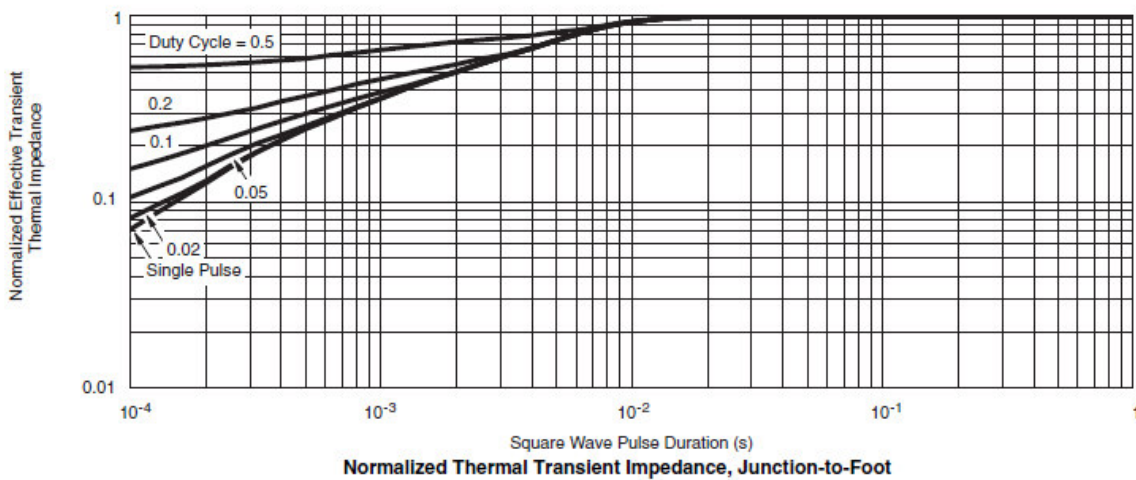
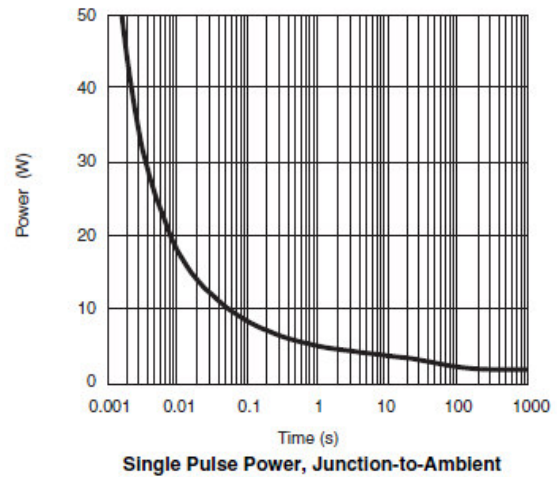
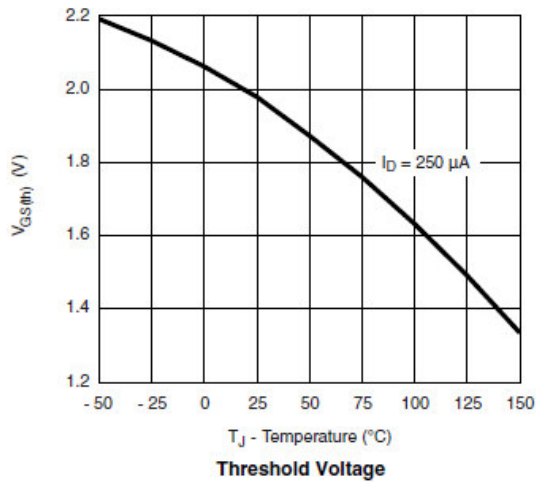
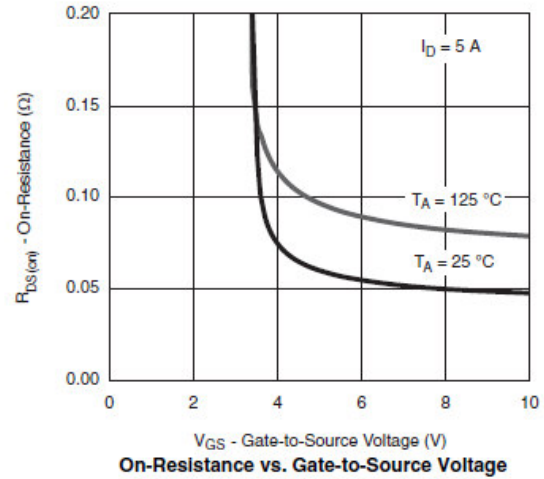
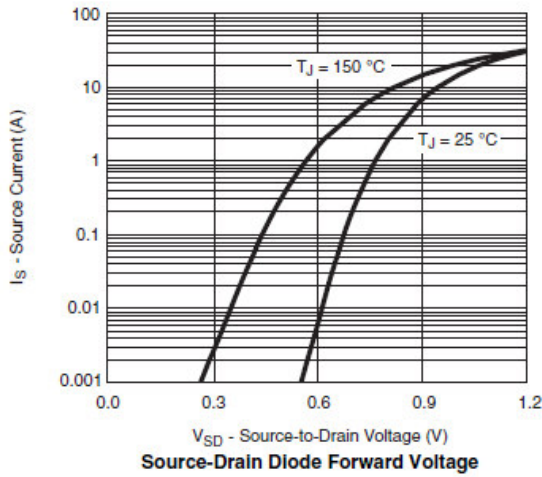
$Q_g$  - Total Gate Charge (nC)  
**Gate Charge**



$T_J$  - Junction Temperature ( $^\circ\text{C}$ )  
**On-Resistance vs. Junction Temperature**



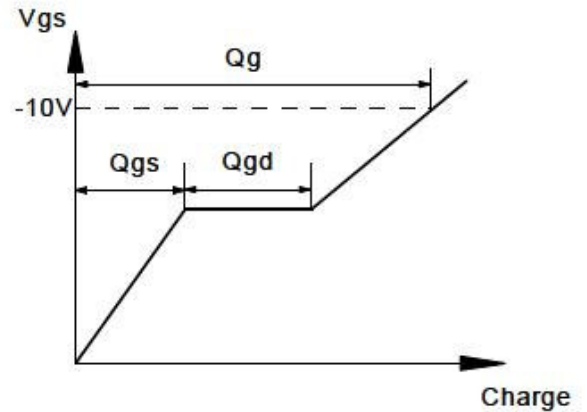
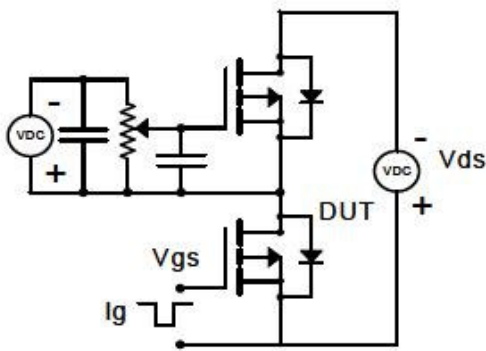
## Typical Characteristics



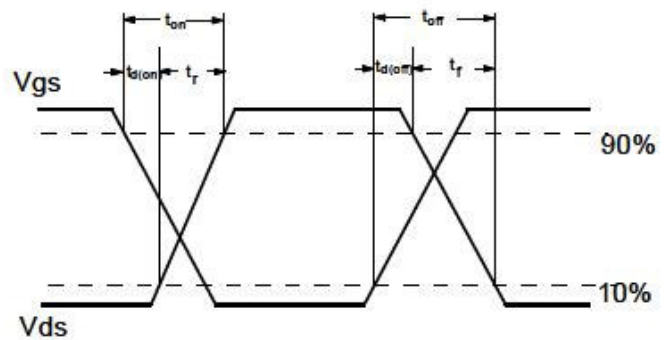
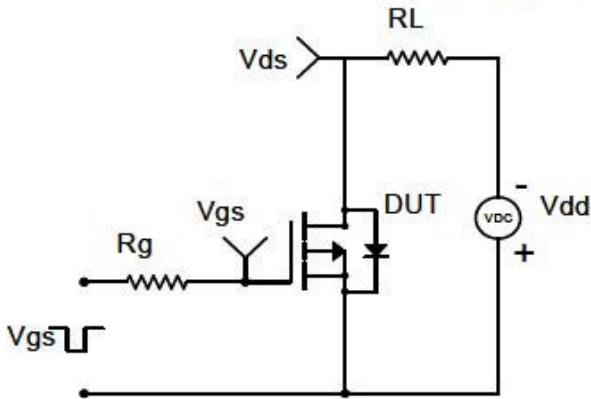


## Typical Characteristics

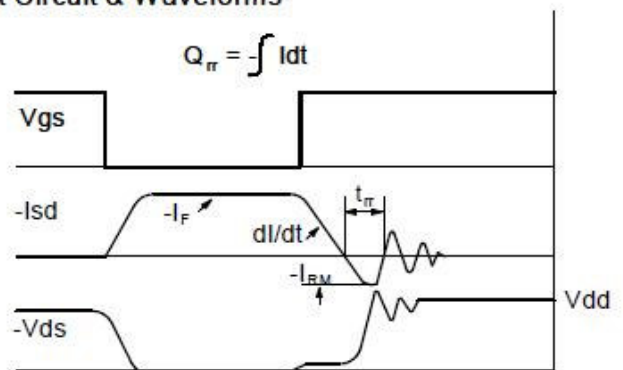
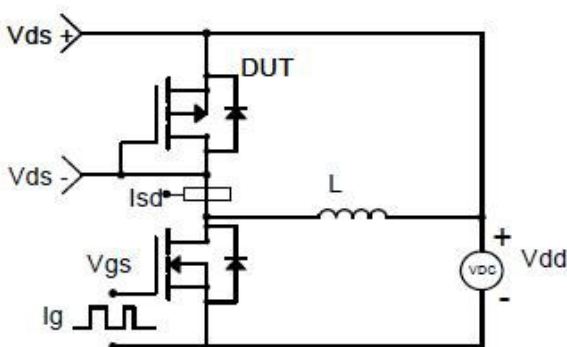
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

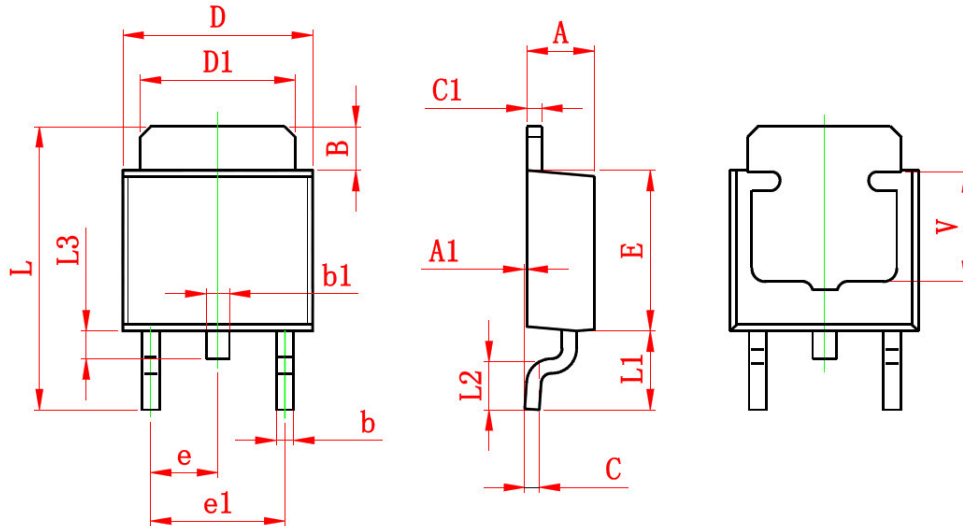


### Diode Recovery Test Circuit & Waveforms





**Package Information ( TO-252-2L )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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